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TRANSMITTAL FORM (to be used for all correspondence after initial filing)	Application Number	10/525,297
	Filing Date	02/15/2005
	First Named Inventor	James S. Im
	Art Unit	2811
	Examiner Name	
Total Number of Pages in This Submission	Attorney Docket Number	A3541-PCT-USA (070050.2717)

ENCLOSURES (Check all that apply)		
<input type="checkbox"/> Fee Transmittal Form	<input type="checkbox"/> Drawing(s)	<input type="checkbox"/> After Allowance Communication to TC
<input type="checkbox"/> Fee Attached	<input type="checkbox"/> Licensing-related Papers	<input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences
<input type="checkbox"/> Amendment/Reply	<input type="checkbox"/> Petition	<input type="checkbox"/> Appeal Communication to TC (Appeal Notice, Brief, Reply Brief)
<input type="checkbox"/> After Final	<input type="checkbox"/> Petition to Convert to a Provisional Application	<input type="checkbox"/> Proprietary Information
<input type="checkbox"/> Affidavits/declaration(s)	<input type="checkbox"/> Power of Attorney, Revocation	<input type="checkbox"/> Status Letter
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SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT			
Firm Name	Baker Botts LLP	Customer No.	21003
Signature			
Printed name	Paul A. Ragusa		
Date	10/11/2005	Reg. No.	38,587

CERTIFICATE OF TRANSMISSION/MAILING	
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Date	10/11/2005

This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : James S. Im

Customer No.: 21003

Serial No. : 10/525,297

Examiner : Not yet assigned

Filed : 02/15/2005

Group Art Unit: 2811

For : PROCESS AND SYSTEM FOR LASER CRYSTALLIZATION PROCESSING
OF FILM REGIONS ON A SUBSTRATE TO MINIMIZE EDGE AREAS, AND
STRUCTURE OF SUCH FILM REGIONS

INFORMATION DISCLOSURE STATEMENT

I hereby certify that this paper is being deposited with the
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October 11, 2005

Date of Deposit

Paul A. Ragusa

Attorney Name

38,587

Patent Reg. No.

[Signature]

Signature

October 11, 2005

Date of Signature

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97(b), applicants bring to the attention of the Examiner the documents listed on the attached Form PTO 1449 and respectfully request that the listed documents be considered by the Examiner and made of record in the above-captioned application. Copies of all U.S. Patents and Applications are not enclosed pursuant to the waiver of 37 CFR 1.98 (a)(2)(i) for all applications filed after June 30, 2003. However, copies of all of the other documents listed on the Form PTO-1449 are enclosed herewith.

NY02:531130.1

This submission does not represent that a search has been made or that no better art exists and does not constitute an admission that the listed documents are material or constitute "prior art." If the Examiner applies the documents as prior art against any claim in the application and applicants determine that the cited documents do not constitute "prior art" under United States law, applicants reserve the right to present to the Office the relevant facts and law regarding the appropriate status of the documents.

Applicants further reserve the right to take appropriate action to establish the patentability of the disclosed invention over the listed documents, should the documents be applied against the claims of the present application.

This Information Disclosure Statement is being before the mailing of a First Office Action. Therefore, applicants believe no fee is due. If any additional fee is due, or if any overpayment has been made, the Commissioner is authorized to charge any such fee or credit any overpayment, to our Deposit Account No. 02-4377.

Respectfully submitted,

BAKER BOTTS L.L.P.

By: 

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Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office	Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant James S. Im	
	Filing Date 02/15/2005	Group 2811
	Examiner Not yet assigned	

U.S. PATENT DOCUMENTS

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
	1	3632205	01/04/1972	Marcy
	2	4234358	11/18/1980	Celler et al.
	3	4309225	01/05/1982	Fan et al.
	4	4382658	05/10/1983	Shields et al.
	5	4456371	06/1984	Lin
	6	4639277	01/27/1987	Hawkins
	7	4691983	09/08/1987	Kobayashi et al.
	8	4727047	02/1988	Bolzer et al.
	9	4758533	07/1988	Magee et al.
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	12	4855014	08/1989	Kakimoto et al.
	13	4870031	09/1989	Suguhara et al.
	14	4940505	07/1990	Schachameyer et al.
	15	4970546	11/1990	Suzuki et al.

NY02:531132.1

Examiner

Date Considered

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	16	4977104	12/11/1990	Sawada et al.
	17	5032233	07/1991	Yu et al.
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	21	5233207	08/1993	Anzai
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	32		5529951	06/1996	Noguchi et al.
	34		5591668	01/1997	Maegawa et al.
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	36		5742426	04/1998	York
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	38		5766989	06/1998	Maegawa et al.
	39		5844588	12/1998	Anderson
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	43		6014944	01/18/2000	Russell et al.
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	45		6081381	06/2000	Shalapenok et al.
	46		6117752	09/12/2000	Suzuki.
	47		6120976	09/2000	Treadwell et al.
	48		6130009	10/2000	Smith et al.

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	49	6130455	10/10/2000	Yoshinouchi
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	52	6169014	01/2001	McCulloch
	53	6172820	01/2001	Kuwahara.
	54	6177301	01/2001	Jung
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	72	6407012	06/18/2002	Miyasaka et al.
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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
	81	6621044	09/01/2003	Jain et al.
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	83	6526585	03/04/2003	Hill
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	88	RE33836	03/03/1992	Resor, III et al.
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	123	2003096489	05/22/2003	Im et al.
	124	2003119286	06/26/2003	Im et al.
	125	2005032249	02/10/2005	Im et al.
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	127	2004061843	04/01/2004	Im
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	130		6582827	06/24/2003	Im
	33		6830993	12/14/2004	Im et al.

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FOREIGN PATENT DOCUMENTS

Exam Initial	No.		Document No.	Publication Date	Country	Translation	
						Yes	No
	90		681316	08/11/1995	EP		
	91		1067593	10/01/2001	EP		
	92		655774	07/17/1996	EP		
	93		2338343	12/15/1999	GB		
	94		2338597	12/22/1999	GB		
	95		2338342	12/15/1999	GB		
	96		2283036	11/20/1990	JP		<u>No</u>
	97		6252048	09/09/1994	JP		<u>No</u>
	98		6283422	10/07/1994	JP		<u>No</u>
	99		7176757	07/14/1995	JP		<u>No</u>
	100		11064883	03/05/1999	JP		<u>No</u>
	101		04033327		JP		<u>No</u>
	102		2001023920	01/26/2001	JP		
	103		62181419	08/08/1987	JP		
	104		9824118	06/04/1998	WO		

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Exam Initial	No.		Document No.	Publication Date	Country	Translation	
						Yes	No
	105		9931719	06/24/1999	WO		<u>No</u>
	106		0014784	03/16/2000	WO		
	107		0118854	03/15/2001	WO		
	108		0118855	03/15/2001	WO		
	109		0171786	09/27/2001	WO		
	110		02031869	04/18/2002	WO		
	111		02086954	05/30/2002	WO		
	112		9745827	12/04/1997	WO		
	113		0242847	05/30/2002	WO		
	114		03046965	06/05/2003	WO		
	115		02086955	10/31/2002	WO		
	116		03018882	03/06/2003	WO		
	117		04017379	02/26/2004	WO		
	118		03084688	10/16/2003	WO		
	119		04017382	02/26/2004	WO		
	120		04017381	02/26/2004	WO		

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Exam Initial	No.		Document No.	Publication Date	Country	Translation	
						Yes	No
	121		04017380	02/26/2004	WO		
	122		04075263	08/19/2003	WO		

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Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)
	132	Im et al., "Controlled Super-Lateral Growth of Si Films for Microstructural Manipulation and Optimization", Phys. Stat. Sol. (a), vol. 166, p. 603 (1998).
	133	S.D. Brotherton et al., "Influence of Melt Depth in Laser Crystallized Poly-Si Thin Film Transistors," 82 J. Appl. Phys. 4086 (1997).
	134	J.S. Im et al., "Crystalline Si Films for Integrated Active-Matrix Liquid-Crystals Displays," 21 MRS Bulletin 39 (1996).
	135	Im et al., "Single-Crystal Si Films for Thin-Film Transistor Devices," Appl. Phys. Lett., Vol 70 (25), p. 3434 (1997).
	136	Sposili et al., "Sequential Lateral Solidification of Thin Silicon Films on SiO ₂ ", Appl. Phys. Lett., vol. 69 (19), p. 2864 (1996).*
	137	Crowder et al., "Low-Temperature Single-Crystal Si TFT's Fabricated on Si Films processed via Sequential Lateral Solidification", IEEE Electron Device Letter, vol. 19 (8), p. 306 (1998).*
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	139	C. E. Nebel, "Laser Interference Structuring of A-Si:H" Amorphous Silicon Technology--1996, San Francisco, CA Apr. 8-12, 1996, Materials Research Society Symposium Proceedings, vol. 420, Pittsburgh, PA.
	140	J. H. Jeon et al., "Two-step laser recrystallization of poly-Si for effective control of grain boundaries", Journal of Non Crystalline Solids, North-Holland Publishing Company, NL, vol. 266-269, May 2000, pp. 645-649.
	141	H. Endert et al., "Excimer Laser: A New Tool for Precision Micromaching," 27 Optical and Quantum Electronics, 1319 (1995).
	142	"Overview of Beam Delivery Systems for Excimer Lasers," Micro/Las Lasersystem GMBH. 1999

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	143	K.H. Weiner et al., "Ultrashallow Junction Formation Using Projection Gas Immersion Laser Doping (PGILD)," A Verdant Technologies Technical Brief, Aug. 20, 1997.
	144	Hau-Riege C.S. et al., "The Effects Microstructural Transitions at Width Transitions on interconnect reliability," Journal of Applied Physics, June 15, 2000, vol. 87, no. 12, pp. 8467-8472
	145	McWilliams et al., "Wafer-Scale Laser Pantography: Fabrication of N-Metal-Oxide-Semiconductor Transistors and Small-Scale Integrated Circuits By Direct-Write Laser-Induced Pyrolytic Reactions," Applied Physics Letters, American Institute of Physics, New York, US, vol. 43, no. 10, Nov. 1983, pp. 946-948
	146	Mariucci et al., "Grain boundary location control by patterned metal film in excimer laser crystallized polysilicon," Proceedings of the Fifth International Conference on Polycrystalline Semiconductors, Schwabisch Gmund, Germany, Sept. 13-18, 1998, vol. 67-68, pp. 175-180
	147	Broadbent et al., "Excimer Laser Processing of Al-1%Cu/TiW Interconnect Layers," 1989 Proceedings, Sixth International IEEE VLSI Multilevel Interconnection Conference, Santa Clara, CA, June 12-13, 1989, pp. 336-345
	148	H.J. Kim and James S. Im, "Grain Boundary Location-Controlled Poly-Si Films for TFT Devices Obtained Via Novel Excimer Laser Process," Abstracts for Symposium of Materials Research Society, Nov.27 to Dec. 2, 1994, p. 230.
	149	S.D. Brotherton, "Polycrystalline Silicon Thin Film Transistors," 10 Semicond. Sci. Tech., pp. 721-738 (1995).
	150	H. Watanabe et al., "Crystallization Process of Polycrystalline Silicon by KrF Excimer Laser Annealing," 33 Japanese J. of Applied Physics Part 1--Regular Papers Short Notes & Review Papers, pp. 4491-98 (1994).
	151	E. Fogarassy et al., "Pulsed Laser Crystallization of Hydrogen-Free a-Si Thin Films for High-Mobility Poly-Si TFT Fabrication," 56 Applied Physics A--Solids and Surfaces, pp. 365-373 (1993).
	152	Y. Miyata et al, "Low-Temperature Polycrystalline Silicon Thin-Film Transistors for Large-Area Liquid Crystal Display," 31 Japanese J. of Applied Physics Part 1--Regular Papers Short Notes & Review Papers, pp. 4559-62 (1992).
	153	Im <i>et al.</i> , "Phase Transformation Mechanisms Involved in Excimer Laser Crystallization of Amorphous Silicon Films," Appl. Phys. Lett., Vol. 63 (14), p. 1969 (1993).

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